

BT137

双向可控硅
TRIAC版本号
201603-A

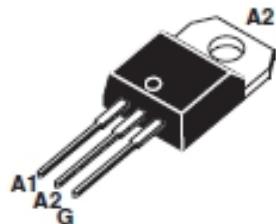
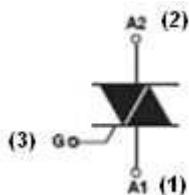
产品概述 GENERAL DESCRIPTION

BT137 双向可控硅采用穿通隔离台面结构，复合玻璃钝化PN结表面保护工艺技术， dv/dt 高，可靠性高，适用于控温、调光、马达控制。

BT137 Triacs is fabricated using separation diffusion processes ,the junction termination areas are passivated with glass. Thanks to highly dv/dt and reliability,the Triacs series is suitable for domestic lighting ,heating and motor speed controllers.

主要参数 MAIN CHARACTERISTICS

| 参数 Parameter | 数值 Value | 单位 Unit |
|-------------------|-----------|---------|
| $I_T(RMS)$ | 8 | A |
| V_{DRM}/V_{RRM} | 600&800 | V |
| $I_{GT(HI)}$ | ≤ 10 | mA |



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产品特性 FEATURES

- dv/dt 高
- 通态压降低
- RoHS环保产品
- Highly dv/dt
- Low on-state voltage
- RoHS Products

应用领域 APPLICATIONS

主要应用于调光、控温、马达控制。

domestic lighting ,heating and motor speed controllers.

极限值(除非另有规定, $T_j=25^\circ\text{C}$) ABSOLUTE RATINGS

(Tj=25°C,unless otherwise specified)

| 符号 Symbol | 参数 Parameter | 数值 Value | 单位 Unit |
|---------------------|--|-------------|------------------------|
| $I_{T(\text{RMS})}$ | RMS 通态电流 RMS on-state current (full sine wave) | 8 | A |
| I_{TSM} | 通态峰值浪涌电流 Non repetitive surge peak on-state current | 65 | A |
| I^2t | I^2t 耗散值 I^2t value for fusino | 21 | A^2s |
| di/dt | 通态电流上升值 Critical rate of rise of on-state current | 50 | $\text{A}/\mu\text{s}$ |
| I_{GM} | 门极峰值电流 Peak gate current | 2 | A |
| $P_{G(\text{AV})}$ | 平均门极耗散功率 Average gate power dissipation | 0.5 | W |
| T_{stg} | 贮存结温范围 Storage junction temperature range | -40~+150 | °C |
| T_j | 工作结温范围 Operating junction temperature range | -40~+125 | °C |

电参数(除非另有规定, $T_j=25^\circ\text{C}$) ELECTRICAL CHARACTERISTICS

(Tj=25°C,unless otherwise specified)

| 参数 Parameter | 符号 Symbol | 规范值 Value | | 单位 Unit | 测试条件 Test Conditions |
|---|--------------|--------------------------|-------------|---------------|--|
| | | D | E | | |
| 触发电流 Gate trigger current | I_{GT} | $I \sim III$ ≤ 5 | ≤ 10 | mA | $V_D=12\text{V}, I_T=0.1\text{A}$ |
| | | IV ≤ 10 | ≤ 25 | | |
| 触发电压 Gate trigger voltage | V_{GT} | I ~ IV | ≤ 1.5 | | V $V_D=12\text{V}, I_T=0.1\text{A}$ |
| 维持电流 Holding current | | I_H | ≤ 20 | ≤ 30 | mA $V_D=12\text{V}, I_T=0.1\text{A}$ |
| 擎住电流 Latching current | | I_L | ≤ 30 | ≤ 35 | mA $V_D=12\text{V}, I_T=0.1\text{A}$ |
| 电压上升率 Rise of off- state voltage | | dv/dt | ≥ 20 | ≥ 50 | V/ μs $V_D=67\%V_{DRM}$ |
| 通态压降 Peak on-state voltage | | V_{TM} | ≤ 1.65 | | V $I_T=10\text{A}$ |
| 断态漏电流 Peak repetitive forward blocking current | I_{DRM} | ≤ 10 | | μA | $V_{RRM}=V_{DRM}, T_j = 25^\circ\text{C}$ |
| | | ≤ 0.5 | | mA | $V_{RRM}=V_{DRM}, T_j = 125^\circ\text{C}$ |

热特性 THERMAL RESISTANCES

| 符号 Symbol | 参数 Parameter | 数值 Value | 单位 Unit |
|---------------|----------------------|----------|---------|
| $R_{th(j-c)}$ | Junction to case(AC) | 1.8 | °C/W |
| $R_{th(j-a)}$ | Junction to ambient | 60 | °C/W |

特征曲线 ELECTRICAL CHARACTERISTICS (CURVES)

图1 最大耗散功率与RMS通态电流关系
Fig.1. Maximum Power Dissipation Versus
on-state current

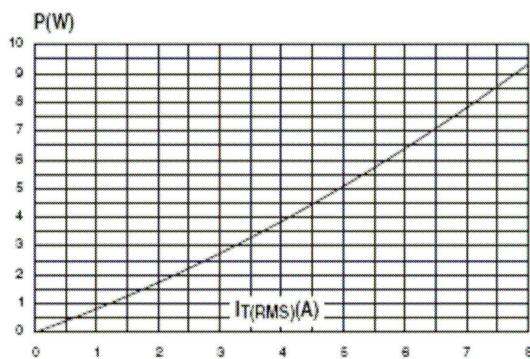


图3 通态特性
Fig.3.On-State Characteristics

图2 RMS通态电流与T_c温度关系
Fig.2. RMS On-state Current Versus TL
on-state current

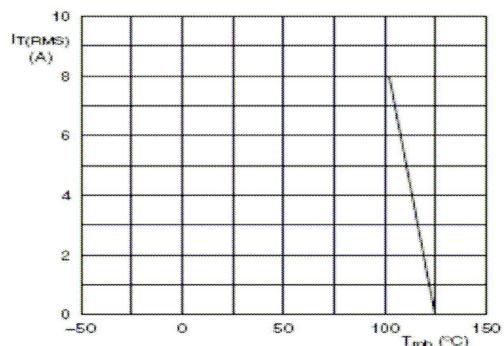


图4 通态浪涌峰值电流与周期数关系
Fig.4.Surge Peak On-state Current Versus Number Cycles

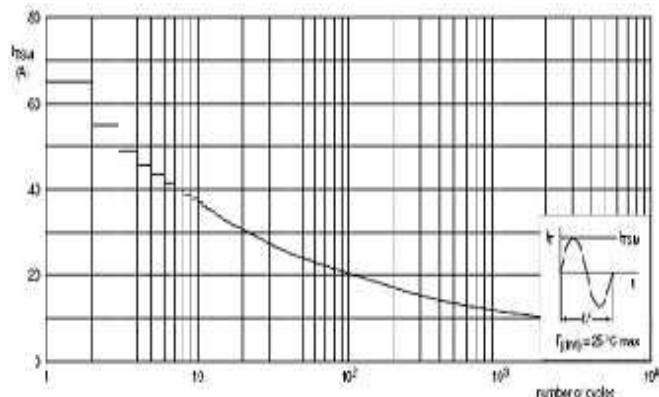
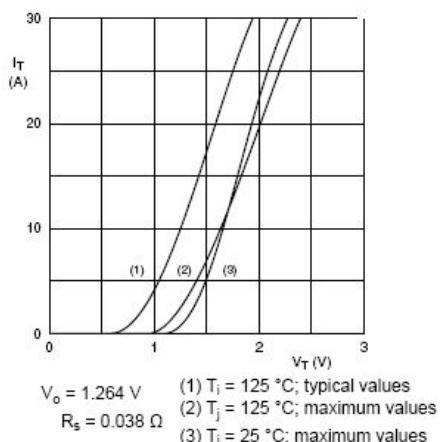
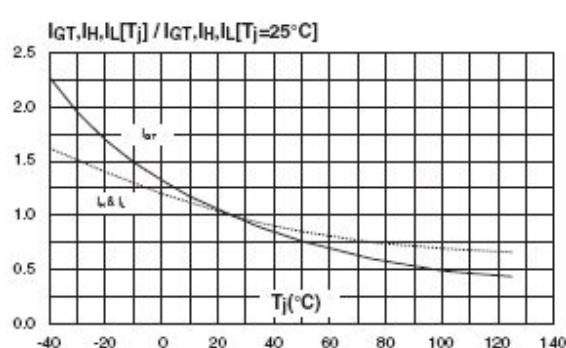


图5 I_{GT}、I_H、I_L相对值（相对于25℃）与结温关系
Fig.5.Relative Variation Of Gate Trigger Current
, Holding Current And Latching Current Versus Junction Temperature (Typical Value)



封装尺寸 PACKAGE MECHANICAL DATA

TO-220AB

| Ref. | Dimensions | | | | | |
|------|-------------|-------|-------|--------|-------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| A | 15.20 | | 15.90 | 0.598 | | 0.625 |
| a1 | | 3.75 | | | 0.147 | |
| a2 | 13.00 | | 14.00 | 0.511 | | 0.551 |
| B | 10.00 | | 10.40 | 0.393 | | 0.409 |
| b1 | 0.61 | | 0.88 | 0.024 | | 0.034 |
| b2 | 1.23 | | 1.32 | 0.048 | | 0.051 |
| C | 4.40 | | 4.60 | 0.173 | | 0.181 |
| c1 | 0.49 | | 0.70 | 0.019 | | 0.027 |
| c2 | 2.40 | | 2.72 | 0.094 | | 0.107 |
| e | 2.40 | | 2.70 | 0.094 | | 0.106 |
| F | 6.20 | | 6.70 | 0.244 | | 0.264 |
| Ø1 | 3.70 | | 3.85 | 0.146 | | 0.151 |
| I4 | 15.80 | 16.40 | 16.80 | 0.622 | 0.646 | 0.661 |
| L | 2.65 | | 2.95 | 0.104 | | 0.116 |
| I2 | 1.14 | | 1.70 | 0.044 | | 0.066 |
| I3 | 1.14 | | 1.70 | 0.044 | | 0.066 |
| M | | 2.60 | | | 0.102 | |

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